

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FIL	ING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/695,159	10/695,159 1		Tatsuya Usami	NEC 01207 DIV2	7174	
27667	7590	12/20/2004	EXAMINE		INER	
HAYES, S			LEE, HSIE	LEE, HSIEN MING .		
130 W. CUS TUCSON, A		EET	ART UNIT	PAPER NUMBER		
1000011, 1	22 00,01			2823		
				DATE MAIL ED. 12/20/200	DATE MAILED: 12/20/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
	10/695,159	USAMI, TATSUYA				
Office Action Summary	Examiner	Art Unit				
	Hsien-ming Lee	2823 .				
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPL' THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl If NO period for reply is specified above, the maximum statutory period or - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time y within the statutory minimum of thirty (30) days will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on						
2a) This action is FINAL . 2b) ☐ This	s action is non-final.					
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims						
4) Claim(s) 14-18 is/are pending in the application 4a) Of the above claim(s) is/are withdrays 5) Claim(s) is/are allowed. 6) Claim(s) 14-16 is/are rejected. 7) Claim(s) 17 and 18 is/are objected to. 8) Claim(s) are subject to restriction and/or	wn from consideration.					
Application Papers						
9) The specification is objected to by the Examine						
10)⊠ The drawing(s) filed on <u>28 October 2003</u> is/are: a)⊠ accepted or b)□ objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Ex						
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 09/910, 994 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. **NSIEN-MING LEEP PRIMARY EXAMINED.**						
Attachment(s)		PRIMARY EXAMINATE (PTO-413)				
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 102803. 	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:					

Application/Control Number: 10/695,159

Art Unit: 2823

DETAILED ACTION

Page 2

Information Disclosure Statement

1. The information disclosure statement filed 10/28/03 fails to comply with the provisions of 37 CFR 1.97, 1.98 and MPEP § 609 because the Patent Number does **not match** the name, date, related class. See remark in Form 1449. It has been placed in the application file, but the information referred to therein has not been considered as to the merits. Applicant is advised that the date of any re-submission of any item of information contained in this information disclosure statement or the submission of any missing element(s) will be the date of submission for purposes of determining compliance with the requirements based on the time of filing the statement, including all certification requirements for statements under 37 CFR 1.97(e). See MPEP § 609 ¶ C(1).

Double Patenting

2. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

3. Claims 14-16 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claim 1 of U.S. Patent No. 6,514,852. Although the conflicting claims are not identical, they are not patentably distinct from each other because the

instant invention teaches the substantially same subject matter as that of US '852, regardless of minor obvious wording variation.

US '852 claims not only all limitations as recited in claim 14 of the instant invention but also further claims that the first through third hard masks are consecutively formed and having different etching rates in an etching condition (col. 10, lines 28-31), which is equivalent to the subject matter of claim 16 of the instant invention.

Therefore, it would have been obvious to one of the ordinary skill in the art, at the time of the invention was made, to comprehend that claims 14 and 16 of the instant invention are **not** patentably distinct from US'852, since both claim **substantially same** subject matter.

In re claim 15, it would have been obvious to one of the ordinary skill in the art, at the time of the invention was made, to recognize that US'852 also implies that three hard mark films are made of different material since three hard mask films in US'852 have different etching rate (col. 10, lines 30-31).

Allowable Subject Matter

- 4. Claims 17 and 18 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- The following is a statement of reasons for the indication of allowable subject matter:

 The closest prior art of record, Grill et al. to US 6,140,226, teach a related art,

 comprising:
 - forming first level interconnections 4 overlying a substrate 2;

Art Unit: 2823

• consecutively forming first 7/8 and second 10/12 dielectric films on said first level interconnections 4 (Fig.6A);

- consecutively forming first 66, second 68 and third 70 hard mask films on said second dielectric film 10/12 (Fig.6A), said first 66 through third 70 hard mask films being insulating films;
- selectively etching said third hard mask film 70 to form a trench pattern on said third hard mask film 70, said trench pattern partially overlapping said through-hole pattern (Fig.6E);
- selectively etching said first hard mask film 66 by using said second hard mask film as an etching mask to form said through-hole pattern on said first hard mask film 66 (Fig.6F);
- selectively etching said second dielectric film 10/12 by using said first hard mask film 66 as an etching mask to form first through-holes in said second dielectric film 10/12 based on said through-hole pattern (Fig.6G); and
- selectively etching said first dielectric film to form therein second through-holes
 communicated with respective said first through-holes for exposing part of said first
 level interconnections through said first and second through-holes.

In contrast, Grill et al. neither teach nor suggest selectively etching said second and third hard mask films to form a through-hole pattern on said second and third hard mask films; selectively etching said first and second hard mask films and a top portion of said first dielectric film by using said third hard mask film as an etching mask to form trenches in said first and second hard mask films and said top portion of said second dielectric film based on said trench

Application/Control Number: 10/695,159 Page 5

Art Unit: 2823

pattern (claim 14); forming a *first anti-reflection film* is formed *on* said *third* hard mask (claim 17); and forming a *second anti-reflection film* is formed *on* said *third* hard mask for filling the first through-hole pattern (claim 18).

6. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Hsien-ming Lee whose telephone number is 571-272-1863. The

examiner can normally be reached on Tuesday-Thursday ($8:00 \sim 6:00$).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik

Chaudhuri can be reached on 571-272-1855. The fax phone number for the organization where

this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Hsien-ming Lee Primary Examiner Art Unit 2823

Dec. 15, 2004

HSIEN-MING LEE PRIMARY EXAMINATE 12/15/2004